

Description

The HXY4828S uses advanced trench technology to provide excellent R_{DS(ON)}, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

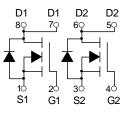
 $V_{DS} = 60V \ I_D = 6.5 \ A$ $R_{DS(ON)} < 36m\Omega @ V_{GS} = 10 \ V$ $R_{DS(ON)} < 48m\Omega @ V_{GS} = 4.5 \ V$

Application

Battery protection Load switch Uninterruptible power supply



SOP-8



Dual N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY4828S	SOP-8	4828 XXX YYYY	3000

Absolute Maximum Ratings@Tj=25°C(unless otherwise specified)

Symbol	Parameter	Rating	Units	
V _{DS}	Drain-Source Voltage	60	V	
V _{GS}	Gate-Source Voltage	<u>+</u> 20	V	
I₀@T₄=25℃	Drain Current, V _{GS} @ 4.5V ³	6.5	Α	
I₀@T₄=70°C	Drain Current, V _{GS} @ 4.5V ³	5	A	
Ідм	Pulsed Drain Current ¹	30	A	
P _D @T _A =25℃	Total Power Dissipation	2.1	W	
Тѕтс	Storage Temperature Range	-55 to 150	°C	
TJ	Operating Junction Temperature Range	-55 to 150	°C	
Rthj-a	Maximum Thermal Resistance, Junction- ambient ³	60	°C/W	



Dual N-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_A=25 $^{\circ}$ C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	60		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-		1	μA
Gate-Body Leakage Current	I _{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	±100	nA
On Characteristics (Note 3)			•			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.0	1.4	2.0	V
	R _{DS(ON)}	V _{GS} =10V, I _D =6A		32	36	mΩ
Drain-Source On-State Resistance		V _{GS} =4.5V, I _D =4A		34	48	mΩ
Forward Transconductance	g fs	V _{DS} =5V,I _D =6A		20	-	S
Dynamic Characteristics (Note4)	L L					
Input Capacitance	Clss	N/ 051/11/ 01/		1920		PF
Output Capacitance	Coss	$V_{DS}=25V, V_{GS}=0V,$		155		PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz		116		PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	8	-	nS
Turn-on Rise Time	t _r	V_{DS} =30V, R _L =4.7 Ω	-	5	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{GEN} =3 Ω	-	29	-	nS
Turn-Off Fall Time	t _f		-	6	-	nS
Total Gate Charge	Qg	N/ 201/1 CA	-	50	-	nC
Gate-Source Charge	Q _{gs}	V _{DS} =30V,I _D =6A, V _{GS} =10V	-	8	-	nC
Gate-Drain Charge	Q _{gd}	V _{GS} -10V	-	16	-	nC
Drain-Source Diode Characteristic	cs					
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =6A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	7	Α
Reverse Recovery Time	t _{rr}	TJ = 25°C, I _F =7A	-	35	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	43	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD))

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

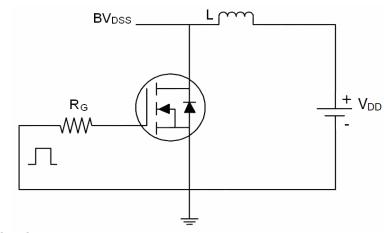
2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

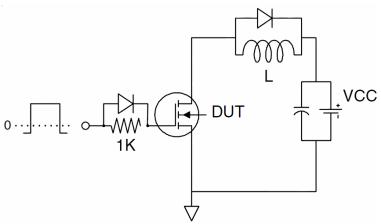
4. Guaranteed by design, not subject to production



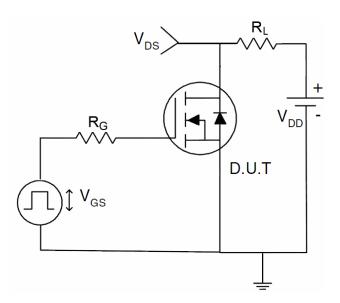
Test Circuit 1) E_{AS} test Circuits



2) Gate charge test Circuit

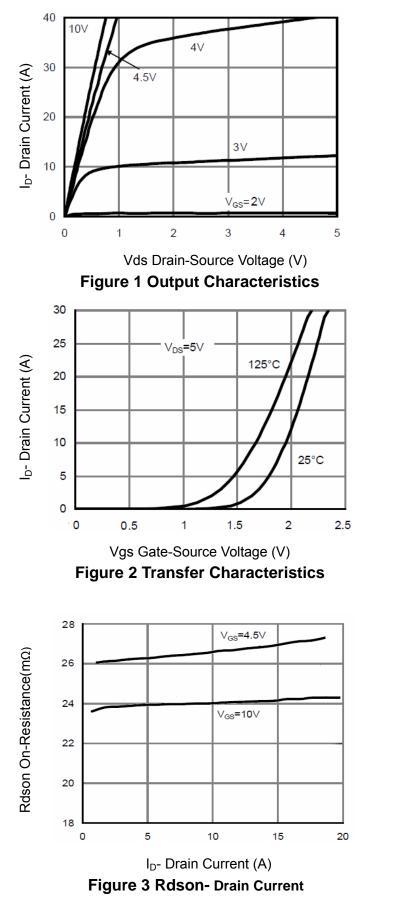


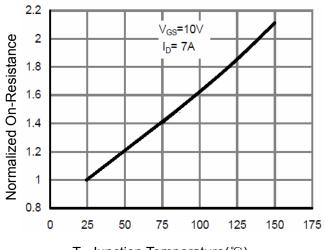
3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)





 $\mathsf{T}_{\mathsf{J}} ext{-}\mathsf{Junction}$ Temperature($^{\circ}\!\!\mathbb{C}$)

Figure 4 Rdson-JunctionTemperature

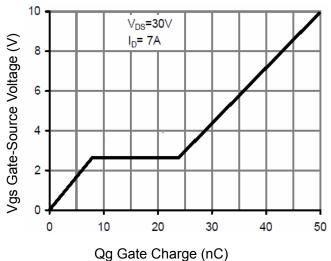


Figure 5 Gate Charge

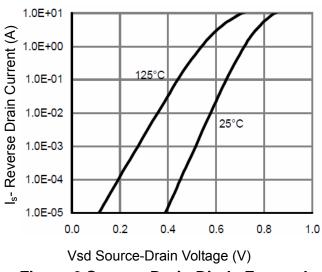
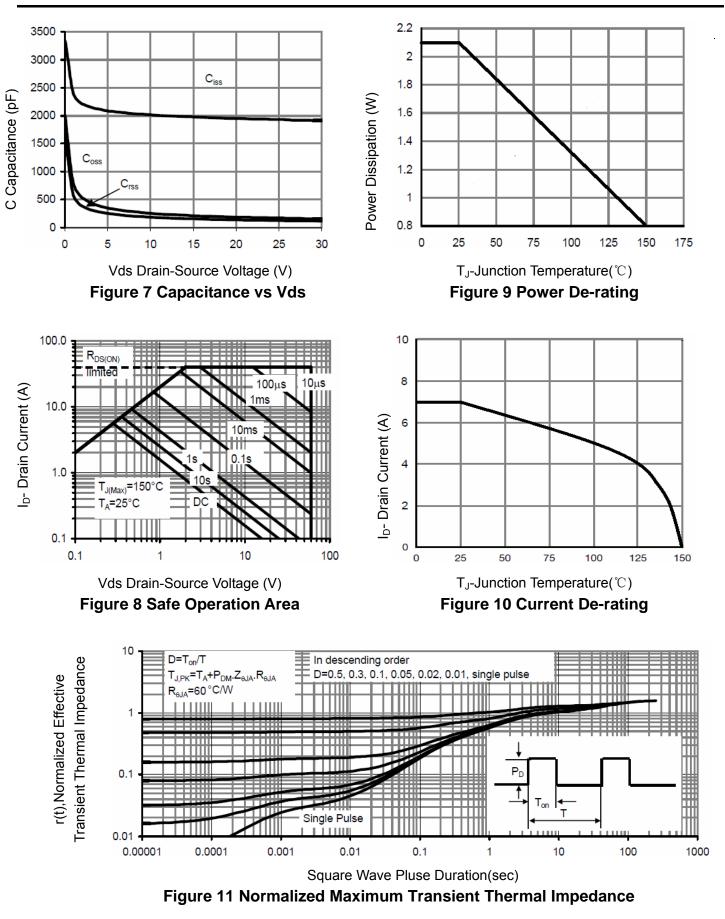


Figure 6 Source- Drain Diode Forward

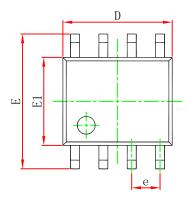


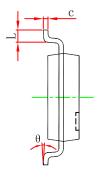
HXY4828S Dual N-Channel Enhancement Mode MOSFET

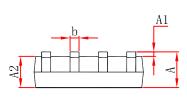




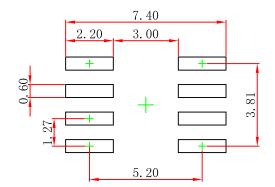
SOP-8 Package Outline Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
А	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
с	0.170	0.250	0.007	0.010	
D	4.800	5.000	0.189	0.197	
e	1.270 (BSC)		0.050 (BSC)		
E	5.800	6.200	0.228	0.244	
E1	3.800	4.000	0.150	0.157	
L	0.400	1.270	0.016	0.050	
θ	0 °	8°	0 °	8°	



Note: 1.Controlling dimension:in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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